

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	752	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon	USPAT	OR	ON	2005/04/02 09:17
S2	0	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and (polysilicon adj floating adj electrode)	USPAT	OR	ON	2005/04/02 09:18
S3	23	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and electrode and (tunnel adj oxide) and negative and positive and voltage and transistor and band	USPAT	OR	ON	2005/04/02 09:20
S4	0	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and electrode and (tunnel adj oxide) and negative and positive and voltage and transistor and band and (doped adj polysilicon)	USPAT	OR	ON	2005/04/02 09:20
S5	5	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and electrode and (tunnel adj oxide) and negative and positive and voltage and transistor and band and (doped adj polysilicon)	USPAT	OR	ON	2005/04/02 09:42
S6	1	("5761125").PN.	USPAT	OR	OFF	2005/04/02 09:44
S7	974	(first adj conductivity) and (second adj conductivity) and type and n-type and p-type and region and third and fourth and trench	USPAT	OR	ON	2005/04/04 11:23
S8	6	(first adj conductivity adj type) and (second adj conductivity adj type) and type and n-type and p-type and region and third and fourth and trench and crystallographic and orientation	USPAT	OR	ON	2005/04/04 11:38

S9	6	S8 and (plug or metal or gate or trench or contact or insulator or transistor or MOS or first or second or third or fourth or region or conductive or material or insulation or insulating or plurality or dope or doped or polysilicon or surface)	USPAT	OR	ON	2005/04/04 11:41
S10	1	("6836001").PN.	USPAT	OR	OFF	2005/04/04 11:41
S11	1	S10 and (plug or metal or gate or trench or contact or insulator or transistor or MOS or first or second or third or fourth or region or conductive or material or insulation or insulating or plurality or dope or doped or polysilicon or surface or conductivity or NMOS or orientation or crystallographic)	USPAT	OR	ON	2005/04/04 11:42
S12	1	"6700175".PN.	USPAT; USOCR	OR	ON	2005/04/04 11:42
S13	1	"6670673".PN.	USPAT; USOCR	OR	ON	2005/04/04 11:44
S14	1	"20040026735".PN.	US-PGPUB	OR	ON	2005/04/04 11:44
S15	1	"20040016959".PN.	US-PGPUB	OR	ON	2005/04/04 11:45
S16	1	"6525375".PN.	USPAT; USOCR	OR	ON	2005/04/04 11:45
S17	1	"5828101".PN.	USPAT; USOCR	OR	ON	2005/04/04 11:45